

2SB726

Silicon PNP epitaxial planer type

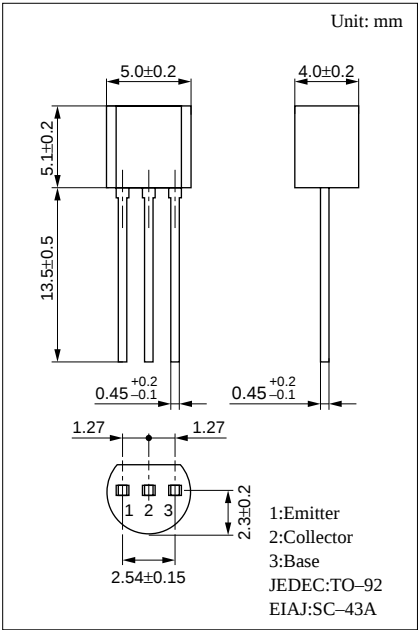
For general amplification

Features

- High foward current transfer ratio h_{FE} .
- High collector to emitter voltage V_{CEO} .

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	-80	V
Collector to emitter voltage	V_{CEO}	-80	V
Emitter to base voltage	V_{EBO}	-5	V
Collector current	I_C	-100	mA
Collector power dissipation	P_C	250	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 ~ +150	°C

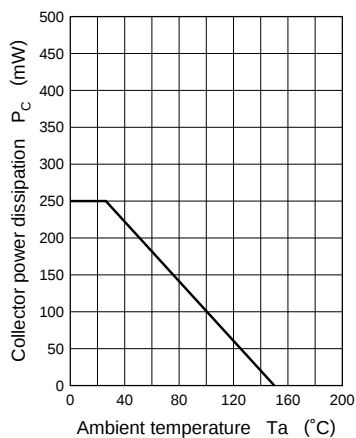
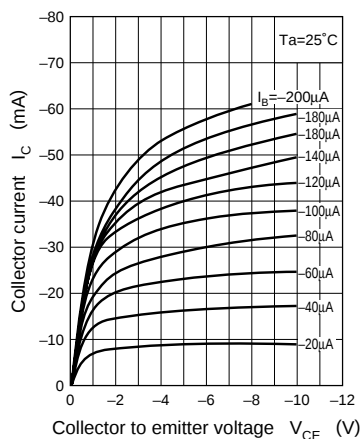
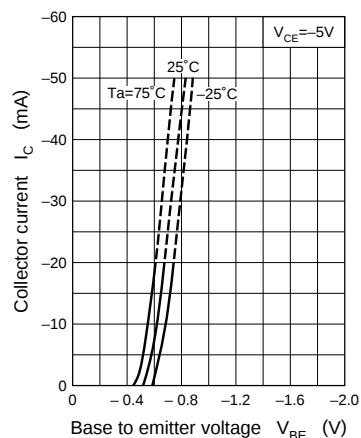
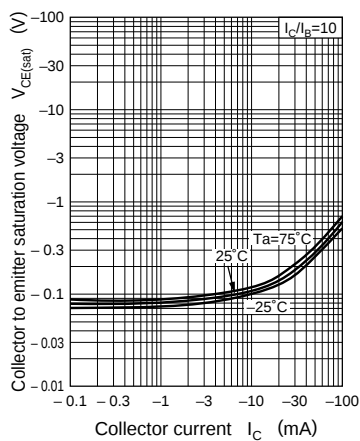
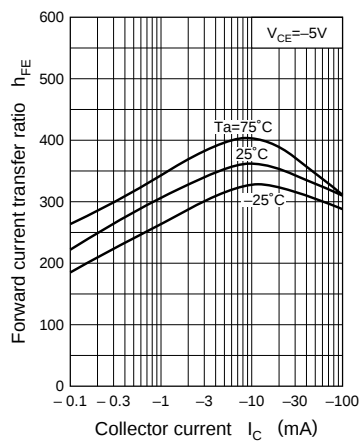
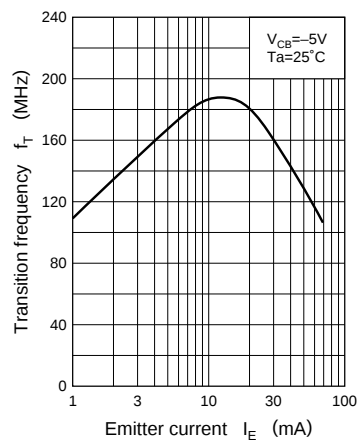


Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -10V, I_E = 0$			-100	nA
	I_{CEO}	$V_{CE} = -10V, I_B = 0$			-1	μA
Collector to base voltage	V_{CBO}	$I_C = -10\mu A, I_E = 0$	-80			V
Collector to emitter voltage	V_{CEO}	$I_C = -2mA, I_B = 0$	-80			V
Emitter to base voltage	V_{EBO}	$I_E = -10\mu A, I_C = 0$	-5			V
Forward current transfer ratio	h_{FE}^*	$V_{CB} = -5V, I_E = -2mA$	180		700	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -20mA, I_B = -2mA$			-0.6	V
Base to emitter voltage	V_{BE}	$V_{CE} = -1V, I_C = -100mA$		-1	-1.2	V
Transition frequency	f_T	$V_{CB} = -5V, I_E = 2mA, f = 200MHz$		150		MHz

* h_{FE} Rank classification

Rank	R	S	T
h_{FE}	180 ~ 360	260 ~ 520	360 ~ 700

$P_C - T_a$  $I_C - V_{CE}$  $I_C - V_{BE}$  $V_{CE(sat)} - I_C$  $h_{FE} - I_C$  $f_T - I_E$  $C_{ob} - V_{CB}$ 